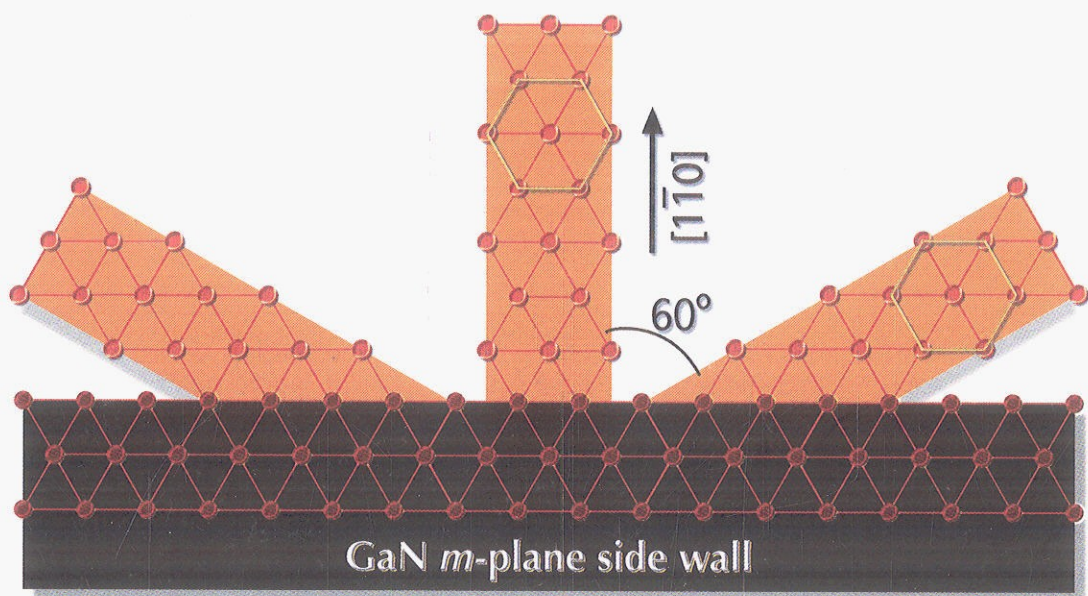


III-Nitride Devices and Nanoengineering



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editor

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